L Number	Hits		DB	Time stamp
1	9	ma-ching-tienin. chen-tsung-chuanin.	USPAT;	2004/07/20 11:49
		hsu-shew-tsuin.	US-PGPUB;	
			EPO; JPO;	
2	452476	resist photoresist photo-resist	DERWENT USPAT;	2004/07/20 11:50
	132173	photo resist	US-PGPUB;	2004/07/20 11:50
			EPO; JPO;	
			DERWENT	
3	339939	photosensitive photo-sensitive (sensitive	USPAT;	2004/07/20 11:50
		near (photo light energy radiation))	US-PGPUB;	
			EPO; JPO; DERWENT	
4	9231	duv! (deep adj2 (uv ultraviolet ultra-violet	USPAT;	2004/07/20 11:50
		ultra adj violet))	US-PGPUB;	
		·	EPO; JPO;	
5	116700	krf arf f2 "f.sub.2"	DERWENT	
] 3	110/98	KIT dIT 12 "1.Sub.2"	USPAT; US-PGPUB;	2004/07/20 11:50
			EPO; JPO;	
			DERWENT	
6	12147	("157" "193" "248") near (nm! nanometer	USPAT;	2004/07/20 11:51
		nano-meter nano adj meter)	US-PGPUB;	
			EPO; JPO;	
7	275665	(oxide dioxide) near (layer film coating)	DERWENT USPAT;	2004/07/20 11:51
		(US-PGPUB;	2001/07/20 11.51
			EPO; JPO;	
	01000		DERWENT	
8	21899	etchstop etch-stop etch adj stop hardmask hard-mask hard adj mask	USPAT;	2004/07/20 11:51
		natu-mask hard adj mask	US-PGPUB; EPO; JPO;	
			DERWENT	
9	1866544	si silicon si-contain\$3 silicon-contain\$3	USPAT;	2004/07/20 11:51
			US-PGPUB;	
			EPO; JPO;	
10	232413	(silicon adj (nitride oxynitride oxy-nitride	DERWENT USPAT;	2004/07/20 11:51
		oxy adj nitride carbide)) "si.sub.3 n.sub.4"	US-PGPUB;	2004/07/20 11.31
		sion sic	EPO; JPO;	
11	7658	(420/211 212 214 217 227 220 220 220 221	DERWENT	
11	7636	(430/311,313,314,317,327,328,330.ccls. 328/694.ccls.)	USPAT; US-PGPUB;	2004/07/20 11:51
		223, 031100121,	EPO; JPO;	
			DERWENT	
13	68211	aspect adj ratio	USPAT;	2004/07/20 11:52
			US-PGPUB;	
			EPO; JPO; DERWENT	
14	2549112	via contact adj hole	USPAT;	2004/07/20 11:53
			US-PGPUB;	
		·	EPO; JPO;	
15	9000	(etchstop etch-stop etch adj stop hardmask	DERWENT USPAT;	2004/07/20 11:54
		hard-mask hard adj mask) with ((si silicon	US-PGPUB;	2001/07/20 11:54
		si-contain\$3 silicon-contain\$3) ((silicon	EPO; JPO;	
		adj (nitride oxynitride oxy-nitride oxy adj	DERWENT	
į		nitride carbide)) "si.sub.3 n.sub.4" sion sic))		
16	7988	((resist photoresist photo-resist)	USPAT;	2004/07/20 11:54
		(photosensitive photo-sensitive (sensitive	US-PGPUB;	
	İ	near (photo light energy radiation)))) with	EPO; JPO;	
		((duv! (deep adj2 (uv ultraviolet	DERWENT	
		ultra-violet ultra adj violet))) (krf arf f2 "f.sub.2") (("157" "193" "248") near		
	ļ	(nm! nanometer nano-meter nano adj meter)))		
20	66778	(cur\$3 near2 (uv ultraviolet ultra-violet	USPAT;	2004/07/20 12:02
		ultra adj violet (duv! (deep adj2 (uv	US-PGPUB;	
ļ	·	ultraviolet ultra-violet ultra adj violet))) light radiation)) photo-cur\$3 photocur\$3	EPO; JPO;	
		, right radiation, photo-curss photocurss	DERWENT	

21	2396	<pre>((resist photoresist photo-resist) (photosensitive photo-sensitive (sensitive near (photo light energy radiation)))) near4 ((cur\$3 near2 (uv ultraviolet ultra-violet ultra adj violet (duv! (deep adj2 (uv ultraviolet ultra-violet ultra adj violet))) light radiation)) photo-cur\$3 photocur\$3)</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/20 12:03
22	4	(((resist photoresist photo-resist) (photosensitive photo-sensitive (sensitive near (photo light energy radiation)))) near4 ((cur\$3 near2 (uv ultraviolet ultra-violet ultra adj violet (duv! (deep adj2 (uv ultraviolet ultra-violet ultra adj violet))) light radiation)) photo-cur\$3 photocur\$3)) same ((oxide dioxide) near (layer film coating)) same ((etchstop etch-stop etch adj stop hardmask hard-mask hard adj mask) with ((si silicon si-contain\$3 silicon-contain\$3) ((silicon adj (nitride oxynitride oxy-nitride oxy adj nitride carbide)) "si.sub.3 n.sub.4" sion sic)))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/20 12:11
23	1051	<pre>((resist photoresist photo-resist) (photosensitive photo-sensitive (sensitive near (photo light energy radiation)))) same ((oxide dioxide) near (layer film coating)) same ((etchstop etch-stop etch adj stop hardmask hard-mask hard adj mask) with ((si silicon si-contain\$3 silicon-contain\$3) ((silicon adj (nitride oxynitride oxy-nitride oxy adj nitride carbide)) "si.sub.3 n.sub.4" sion sic)))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/20 12:12
	34	(((resist photoresist photo-resist) (photosensitive photo-sensitive (sensitive near (photo light energy radiation)))) same ((oxide dioxide) near (layer film coating)) same ((etchstop etch-stop etch adj stop hardmask hard-mask hard adj mask) with ((si silicon si-contain\$3 silicon-contain\$3) ((silicon adj (nitride oxynitride oxy-nitride oxy adj nitride carbide)) "si.sub.3 n.sub.4" sion sic)))) and ((duv! (deep adj2 (uv ultraviolet ultra-violet ultra adj violet))) (krf arf f2 "f.sub.2") (("157" "193" "248") near (nm! nanometer nano-meter nano adj meter))) and (aspect adj ratio)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/20 12:20
25	5585	(aspect adj ratio) with (via contact adj hole)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/20 12:21
27	948	((aspect adj ratio) with (via contact adj hole)) with ("8" "9" "10" "11" "12" "13" "14" "15" "20")	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/20 12:26
29	1734	((aspect adj ratio) with (via contact adj hole)) with (least greater more between range)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/20 12:27
30	1	<pre>(((aspect adj ratio) with (via contact adj hole)) with (least greater more between range)) same ((resist photoresist photo-resist) (photosensitive photo-sensitive (sensitive near (photo light energy radiation)))) same ((etchstop etch-stop etch adj stop hardmask hard-mask hard adj mask) with ((si silicon si-contain\$3 silicon-contain\$3) ((silicon adj (nitride oxynitride oxy-nitride oxy adj nitride carbide)) "si.sub.3 n.sub.4" sion sic)))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/20 12:28

		T		
32	9	The state of the s	USPAT;	2004/07/20 12:28
		hole)) with (least greater more between range)) same ((resist photoresist	US-PGPUB;	
		photo-resist) (photosensitive	EPO; JPO; DERWENT	
		photo-sensitive (sensitive near (photo light	DERWENT	
		energy radiation)))) same (etchstop		
		etch-stop etch adj stop hardmask hard-mask		
	:	hard adj mask)		
31	108		USPAT;	2004/07/20 12:31
		hole)) with (least greater more between	US-PGPUB;	_ = = = = = = = = = = = = = = = = = = =
		range)) and ((resist photoresist	EPO; JPO;	
		photo-resist) (photosensitive	DERWENT	
		photo-sensitive (sensitive near (photo light		
		energy radiation)))) and ((etchstop		
	1	etch-stop etch adj stop hardmask hard-mask		
		hard adj mask) with ((si silicon		
		si-contain\$3 silicon-contain\$3) ((silicon		
		adj (nitride oxynitride oxy-nitride oxy adj		
		nitride carbide)) "si.sub.3 n.sub.4" sion sic)))		
33	18			1
33	10	(((aspect adj ratio) with (via contact adj	USPAT;	2004/07/20 12:36
		hole)) with (least greater more between range)) and ((resist photoresist	US-PGPUB;	
I		photo-resist) (photosensitive	EPO; JPO;	
	1	photo-sensitive (sensitive near (photo light	DERWENT	
		energy radiation)))) and ((etchstop		
		etch-stop etch adj stop hardmask hard-mask		
		hard adj mask) with ((si silicon		
		si-contain\$3 silicon-contain\$3) ((silicon		
		adj (nitride oxynitride oxy-nitride oxy adj		
		nitride carbide)) "si.sub.3 n.sub.4" sion		
		sic))) and ((duv! (deep adj2 (uv		
		ultraviolet ultra-violet ultra adj violet))		
) (("157" "193" "248") near (nm! nanometer		
		nano-meter nano adj meter)))		
34	90	((((aspect adj ratio) with (via contact adj	USPAT;	2004/07/20 12:36
		hole)) with (least greater more between	US-PGPUB;	
		range)) and ((resist photoresist	EPO; JPO;	
		photo-resist) (photosensitive	DERWENT	
		photo-sensitive (sensitive near (photo light		
		energy radiation)))) and ((etchstop		
		etch-stop etch adj stop hardmask hard-mask hard adj mask) with ((si silicon		
		si-contain\$3 silicon-contain\$3) ((silicon		
		adj (nitride oxynitride oxy-nitride oxy adj		
		nitride carbide)) "si.sub.3 n.sub.4" sion		
		sic)))) not ((((aspect adj ratio) with (via		
		contact adj hole)) with (least greater more		
		between range)) and ((resist photoresist		
		photo-resist) (photosensitive		
ł		photo-sensitive (sensitive near (photo light		
	f	energy radiation)))) and ((etchstop		
		etch-stop etch adj stop hardmask hard-mask		
	1	hard adj mask) with ((si silicon		
		si-contain\$3 silicon-contain\$3) ((silicon		
ļ		adj (nitride oxynitride oxy-nitride oxy adj		
		nitride carbide)) "si.sub.3 n.sub.4" sion		
		sic))) and ((duv! (deep adj2 (uv	İ	
	<u> </u>	ultraviolet ultra-violet ultra adj violet))		
	1) (("157" "193" "248") near (nm! nanometer		
		nano-meter nano adj meter))))		